

## MASTER'S THESIS

### Photoluminescence excitation of porous silicon

Ngan, Mei Lun

*Date of Award:*  
1998

[Link to publication](#)

#### **General rights**

Copyright and intellectual property rights for the publications made accessible in HKBU Scholars are retained by the authors and/or other copyright owners. In addition to the restrictions prescribed by the Copyright Ordinance of Hong Kong, all users and readers must also observe the following terms of use:

- Users may download and print one copy of any publication from HKBU Scholars for the purpose of private study or research
- Users cannot further distribute the material or use it for any profit-making activity or commercial gain
- To share publications in HKBU Scholars with others, users are welcome to freely distribute the permanent URL assigned to the publication

# Photoluminescence Excitation of Porous Silicon

NGAN Mei Lun

A thesis submitted in partial fulfillment of the  
requirements for the degree of  
Master of Philosophy

May 1998

Hong Kong Baptist University

## ABSTRACT

TH  
M. PHU  
002NP

Recent research into low dimensional silicon such as porous silicon has shown that it is possible to produce Si-based opto-electronic devices because of quantum confinement effect. Quantum confinement effect causes Si to widen the energy band gap. The band gap becomes pseudo-direct and therefore the luminescence is more efficient. We used two methods to fabricate Si nano-structure. One is anodisation in hydrofluoric acid and the other is photolithography technique to produce regular pattern on silicon. Photoluminescence excitation experiment in difference temperature was performed on porous silicon prepared from n and p type Si(100) by anodisation. It is found that there are multiple peaks in the spectra at some excitation energy. The photoluminescence peak is blue shifted when increasing the excitation energy. And also, the normalised integral photoluminescence intensity as a function of the excitation energy has a maximum around the excitation energy 3.15eV. We used the electronic structure and wave functions of the quantum wire model and the empirical pseudopotential homojunction model to compare with the experiment results. We also obtained the relationship between the integrated photoluminescence intensity and temperature which is caused by quenching of PL from two energy levels.

## CONTENTS

|  |     |
|--|-----|
| ABSTRACT .....   | i   |
| ACKNOWLEDGMENTS .....  | ii  |
| CONTENTS .....   | iii |
| LIST OF TABLES .....   | v   |
| LIST OF FIGURES .....  | vi  |
| <br>   |     |
| Chapter One Introduction .....   | 1   |
| <br>   |     |
| Chapter Two Basic Theory in Low Dimensional Semiconductor Structures ..... | 4   |
| 2.1 Bulk Semiconductor Physics .....                                       | 4   |
| 2.1.1 Crystalline and Amorphous Structure .....                            | 4   |
| 2.1.2 Energy Band Structure .....  | 7   |
| 2.1.3 Optical Theory .....   | 8   |
| 2.2 Review of Low Dimensional Semiconductor Theories .....                 | 12  |
| 2.2.1 Dimensionality .....   | 12  |
| 2.2.2 Electronic Properties .....  | 17  |
| 2.2.3 Optical Properties .....   | 20  |
| <br>   |     |
| Chapter Three Luminescence of Porous Silicon .....                         | 22  |
| 3.1 Basic Theory of Photoluminescence .....                                | 22  |
| 3.1.1 Band-to-Band Transition .....  | 23  |
| 3.1.2 Exciton States Transition .....                                      | 25  |
| 3.1.3 Free-to-Bound Transition .....                                       | 26  |
| 3.1.4 Bound-to-Bound Transition .....                                      | 27  |
| 3.2 Luminescent Mechanisms of Porous Silicon .....                         | 28  |
| 3.2.1 Quantum Confinement .....  | 28  |
| 3.2.2 Surface States .....   | 31  |
| 3.2.3 Silicon Hydrides .....   | 33  |
| 3.2.4 Siloxene Effect .....  | 35  |
| <br>   |     |
| Chapter Four Electronic Structure of Porous Silicon .....                  | 36  |
| 4.1 Semi-empirical Method .....  | 36  |
| 4.2 Implication of the Method .....  | 39  |
| 4.2.1 Energy Level .....   | 39  |
| 4.2.2 Absorption Property .....  | 44  |

|                  |  |     |
|------------------|--|-----|
| Chapter Five     | Fabrication Methods of Silicon Nano-Structure .....                | 49  |
|                  | 5.1 Anodisation Process .....                                      | 49  |
|                  | 5.2 Formation Mechanism .....                                      | 51  |
|                  | 5.2.1 Anodic Dissolution of Silicon .....                          | 52  |
|                  | 5.2.2 Models for Porous Silicon Formation .....                    | 54  |
|                  | 5.2.3 Proposed Structure of Porous Silicon.....                    | 55  |
|                  | 5.3 Factors Affecting Etching Results .....                        | 57  |
|                  | 5.3.1 Doping Concentration .....                                   | 57  |
|                  | 5.3.2 Hydrofluoric Acid Concentration .....                        | 58  |
|                  | 5.3.3 Current Density .....  | 58  |
|                  | 5.3.4 Anodisation Time .....                                       | 60  |
|                  | 5.4 Photolithography and Etching Technology .....                  | 60  |
|                  | 5.4.1 Photolithography Process .....                               | 62  |
|                  | 5.4.2 Reactive Ion Etching Process .....                           | 67  |
|                  | 5.4.3 Potassium Hydroxide Wet Etching .....                        | 67  |
|                  | 5.4.4 Oxidation .....  | 69  |
| Chapter Six      | Experimental Setup .....   | 71  |
|                  | 6.1 Photoluminescence Excitation Measurement .....                 | 71  |
|                  | 6.2 Scanning Electron Microscope (SEM) .....                       | 73  |
|                  | 6.3 Atomic Force Microscope (AFM) .....                            | 75  |
| Chapter Seven    | Measurement Results and Discussions .....                          | 78  |
|                  | 7.1 Fabrication Results .....                                      | 78  |
|                  | 7.1.1 Anodisation .....  | 78  |
|                  | 7.1.2 Photolithography .....                                       | 79  |
|                  | 7.2 PL Excitation Energy Results .....                             | 83  |
|                  | 7.2.1 Multiple Peaks .....   | 83  |
|                  | 7.2.2 Shift of PL Peak .....                                       | 87  |
|                  | 7.2.3 Integrated PL Intensity .....                                | 87  |
|                  | 7.3 Temperature Dependent .....                                    | 92  |
|                  | 7.3.1 Spectrum Profile .....                                       | 92  |
|                  | 7.3.2 Integrated PL Intensity .....                                | 92  |
|                  | 7.4 Discussions .....  | 97  |
|                  | 7.4.1 Multiple Peaks .....   | 97  |
|                  | 7.4.2 Shift of PL Peak .....                                       | 100 |
|                  | 7.4.3 Excitation Energy Dependent of Integrated PL Intensity ..... | 101 |
|                  | 7.4.4 Temperature Dependent of Integrated PL Intensity .....       | 103 |
| Chapter Eight    | Conclusion .....   | 107 |
| References       | .....  | 109 |
| Curriculum Vitae | .....  | 113 |

15634206

TH  
M. PHIL  
1998 PC

A Comparison Between An Ex-ante and Ex-post Test  
of Early Unwinding Strategy in Put-call-futures Arbitrage

PANG Wai Sun

A thesis submitted in partial fulfillment of the requirements  
for the degree of  
Master of Philosophy

June 1998

Hong Kong Baptist University

## Abstract

Previous studies on arbitrage efficiency in derivatives market mainly focus on the cost-of-carry relationship and put-call parity condition. Tucker (1993) introduces the put-call-futures parity condition to investigate the joint efficiency of futures and options markets without incurring the trading of equity. The study applies this parity condition since it provides a superior method to investigate the arbitrage opportunity between futures and options markets. Moreover, it overcomes the obstacles which are associated with the trading in the cash leg of the arbitrage portfolio.

In the study, potential investors are divided into four categories by transaction cost paid. Results show that all investors can make positive profit under the buy-and-hold strategy with ex-post data. However, when ex-ante data is employed, only investors in Category C and D, who are the Exchange members, earn positive profit. The result reconfirms Fung, Cheng & Chan's finding (1997) that the long-futures strategy is more profitable than the short-futures strategy. The results also show that the Exchange members (Category C and D) may make profitable trade under longer execution time lag. Regression results indicate that the parity relationship does hold at both the expiration and non-expiration dates.

Early unwinding strategy is adopted with and without execution time delay to test the arbitrage efficiency of the derivatives markets. Under the early unwinding strategy with ex-post data, it shows that the arbitrage profit is improved for all

investors. When ex-ante data is used, the number of observation is reduced sharply for all kinds of investors. We find that the average arbitrage profits for investors A and B (the individual investor and institutional investor) are below zero or insignificant. We also find that the average profits for investors C and D are lower than that in ex-post analysis. This phenomenon may due to the poor trading signal.



## TABLE OF CONTENTS

|   |      |
|---|------|
| ABSTRACT.....   | I    |
| ACKNOWLEDGEMENTS .....  | III  |
| TABLE OF CONTENTS .....   | IV   |
| LIST OF TABLES.....   | VI   |
| LIST OF FIGURES.....  | VIII |
| INTRODUCTION.....   | 1    |
| LITERATURE REVIEW .....   | 4    |
| 2.1 PROBLEMS ASSOCIATED WITH THE CASH POSITION IN ARBITRAGE.....  | 4    |
| 2.1.1 <i>High trading cost</i> .....  | 4    |
| 2.1.2 <i>Tracking error in replicating the cash index</i> .....   | 5    |
| 2.1.3 <i>Dividend uncertainty</i> .....   | 6    |
| 2.1.4 <i>Restrictions against short-selling of stocks</i> .....   | 7    |
| 2.1.5 <i>Mismatching between the stipulated value of the index for the settlement of the derivative contracts and the closing value of the index portfolio.</i> ..... | 8    |
| 2.1.6 <i>Non-synchronicity of equity trading</i> .....  | 9    |
| 2.2 MOTIVATION .....  | 10   |
| 2.3 PUT-CALL-FUTURES PARITY CONDITION .....   | 10   |
| 2.3.1 <i>Arbitrage Trigger for Buy-and-hold Strategy</i> .....  | 10   |
| 2.3.1A <i>Put-call-futures parity condition with no transaction cost</i> .....  | 12   |
| 2.3.1B <i>Put-call futures parity condition with transaction cost, opportunity cost of margin requirement, bid-ask spread and interest rate differential</i> .....    | 15   |
| 2.3.1B.I <i>Put-call futures parity condition excluding interest rate differential</i> .....  | 15   |
| 2.3.1B.II <i>Put-call futures parity condition including interest rate differential</i> .....   | 16   |
| 2.3.2 <i>Arbitrage Trigger for Early Unwinding</i> .....  | 18   |
| DATA AND METHODOLOGY .....  | 23   |
| 3.1 DATA.....   | 23   |
| 3.1.1 <i>HSI Futures and Options Contracts</i> .....  | 23   |
| 3.2 METHODOLOGY.....  | 24   |
| 3.2.1 <i>Methods in handling Non-executability and Non-synchronicity of Trade</i> .....   | 24   |
| 3.2.2 <i>One-minute Matching Criterion</i> .....  | 25   |
| 3.2.3 <i>Filtering Procedures</i> .....   | 25   |
| 3.2.4 <i>Commission, Exchange Trading Fees and Levies</i> .....   | 27   |
| 3.2.5 <i>Interest Rates</i> .....   | 28   |
| 3.2.6 <i>Margin Requirement</i> .....   | 29   |
| 3.2.7 <i>Measurement of Spread Cost</i> .....   | 29   |
| 3.2.7A <i>Bid-ask spread for futures contract</i> .....   | 29   |
| 3.2.7B <i>Bid-ask spread for options contract</i> .....   | 31   |
| 3.2.8 <i>Trading Cost</i> .....   | 33   |
| 3.2.9 <i>Benefit from Early Unwinding</i> .....   | 34   |

|                                       |            |
|---------------------------------------|------------|
| <b>RESULTS AND DISCUSSIONS.....</b>   | <b>35</b>  |
| 4.1 OUTLINE .....                     | 35         |
| 4.2 BUY-AND-HOLD STRATEGY .....       | 35         |
| 4.2.1 <i>Ex-post Analysis:</i> .....  | 35         |
| 4.2.2 <i>Ex-ante Analysis:</i> .....  | 44         |
| 4.3 EARLY UNWINDING STRATEGY .....    | 58         |
| 4.3.1 <i>Ex-post Analysis:</i> .....  | 58         |
| 4.3.2 <i>Ex-ante Analysis:</i> .....  | 68         |
| <b>CONCLUSION .....</b>               | <b>80</b>  |
| 5.1 CONTRIBUTIONS .....               | 80         |
| 5.2 CONCLUSION AND IMPLICATIONS ..... | 81         |
| 5.3 LIMITATIONS .....                 | 82         |
| <b>APPENDIX A .....</b>               | <b>83</b>  |
| <b>APPENDIX B .....</b>               | <b>92</b>  |
| <b>APPENDIX C .....</b>               | <b>94</b>  |
| <b>REFERENCES.....</b>                | <b>102</b> |
| <b>CURRICULUM VITAE.....</b>          | <b>106</b> |